Manipulating Energy Storage Characteristics of Ultrathin Boron Carbide Monolayer Under Varied Scandium Doping

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S1 Initial and final geometries of all the possible binding configurations of Sc on BC_3 sheet. Binding energies calculated by van der Waals induced calculations are also given.

1. Input Geometry:









S2 Initial and final geometries of all the possible binding configurations of H_2 on $BC_3@Sc$ sheet. Adsorption energies calculated by van der Waals induced calculations are also given.



S3 Top and side views of Isosurface charge densities of (a) $BC_3@Sc-H_2$ and (b) $BC_3@Sc-5H_2$ Cyan and yellow colours indicate the accumulation and depletion of charge respectively.